SHARP

To ;

PRELIMINARY

SPECIFICATIONS

Product Type   64k   SRAM

LH5164AT−80L

Model No.   (LH516AZE)

*This specifications contains 11 pages including the cover and appendix.
If you have any objections, please contact us before issuing purchasing order.

CUSTOMERS ACCEPTANCE

DATE:

BAY:

PRSENTED

BY: _T. Kuzumoto_
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REVIEWED BY: PREPARED BY:

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Tenri Integrated Circuits Group
SHARP CORPORATION

SHARP

LH516AZE

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(1) The products covered herein are designed and manufactured for the following application areas. When using the products covered herein for the equipment listed in Paragraph (2), even for the following application areas, be sure to observe the precautions given in Paragraph (2). Never use the products for the equipment listed in Paragraph (3).
- Office electronics
- Instrumentation and measuring equipment
- Machine tools
- Audiovisual equipment
- Home appliances
- Communication equipment other than for trunk lines

(2) Those contemplating using the products covered herein for the following equipment which demands high reliability, should first contact a sales representative of the company and then accept responsibility for incorporating into the design fail-safe operation, redundancy, and other appropriate measures for ensuring reliability and safety of the equipment and the overall system.

- Control and safety devices for airplanes, trains, automobiles, and other transportation equipment
- Mainframe computers
- Traffic control systems
- Gas leak detectors and automatic cutoff devices
- Rescue and security equipment
- Other safety devices and safety equipment, etc.

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- Aerospace equipment
- Communications equipment for trunk lines
- Control equipment for the nuclear power industry
- Medical equipment related to life support, etc.

(4) Please direct all queries and comments regarding the interpretation of the above three Paragraphs to a sales representative of the company.

● Please direct all queries regarding the products covered herein to a sales representative of the company.

Contents

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1. Decription

The LH5164AT-80L is a static RAM organized as 8,192×8 bit with provides low-power standby mode.
It is fabricated using silicon-gate CMOS process technology.

Features

○ Access Time   · · · ·   80 ns (Max.)

○ Operating current   · · · ·   55 mA (Max.)

    · · · ·   10 mA (Max. t_{RC}, $t_{WC} = 1 \mu s$)

○ Standby current   · · · ·   1.0 μA (Max.)

○ Data retention current   · · · ·   0.2 μA (Max. $V_{CCDR} = 3V$, Ta = 25℃)

○ Single power supply   · · · ·   5 V ± 10%

○ Operating temperature   · · · ·   −10℃ to +70℃

○ Fully static operation

○ Three-state output

○ Not designed or rated as radiation hardened

○ 28 pin TSOP (TSOP28-P-0813) plastic package

○ P-type bulk silicon

2. Pin Configuration

```
$\overline{OE}$     1○                          28   $A_{10}$
$A_{11}$    2                           27   $\overline{CE}_1$
$A_9$      3                           26   $I/O_8$
$A_8$      4                           25   $I/O_7$
$CE_2$     5                           24   $I/O_6$
$\overline{WE}$     6                           23   $I/O_5$
$V_{cc}$    7        (Top View)         22   $I/O_4$
$NC$       8                           21   $GND$
$A_{12}$    9                           20   $I/O_3$
$A_7$     10                           19   $I/O_2$
$A_6$     11                           18   $I/O_1$
$A_5$     12                           17   $A_0$
$A_4$     13                           16   $A_1$
$A_3$     14                           15   $A_2$
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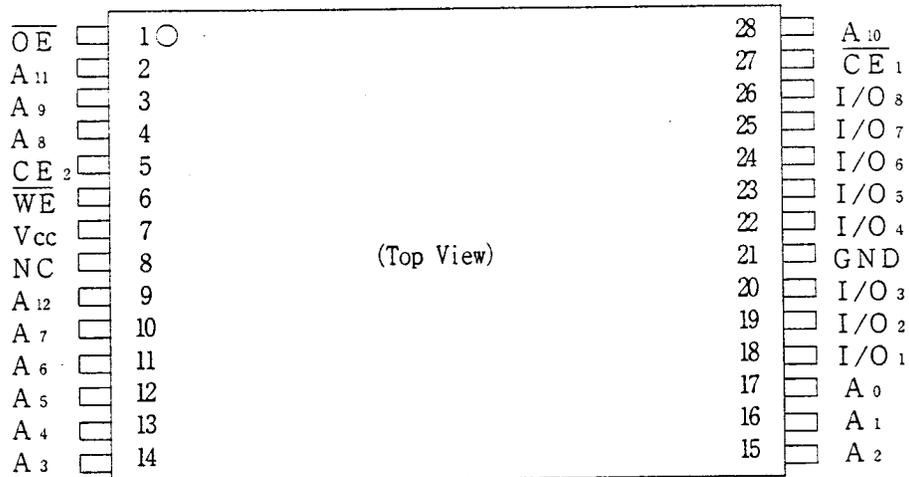
Pin Name	Function
A_0 to A_{12}	Address inputs
$\overline{CE}_1$ / CE_2	Chip enable
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
I/O_1 to I/O_8	Data inputs/outputs
V_{cc}	Power supply
GND	Ground
NC	Non connection

3. Truth Table

$\overline{CE_1}$	CE_2	$\overline{WE}$	$\overline{OE}$	Mode	I/O_1 to I/O_8	Supply current
H	*	*	*	Standby	High impedance	Standby (I_{SB})
*	L	*	*	Standby	High impedance	Standby (I_{SB})
L	H	L	*	Write	Data input	Active (I_{cc})
L	H	H	L	Read	Data output	Active (I_{cc})
L	H	H	H	Read	High impedance	Active (I_{cc})

(*=Don't Care, L=Low, H=High)

4. Block Diagram
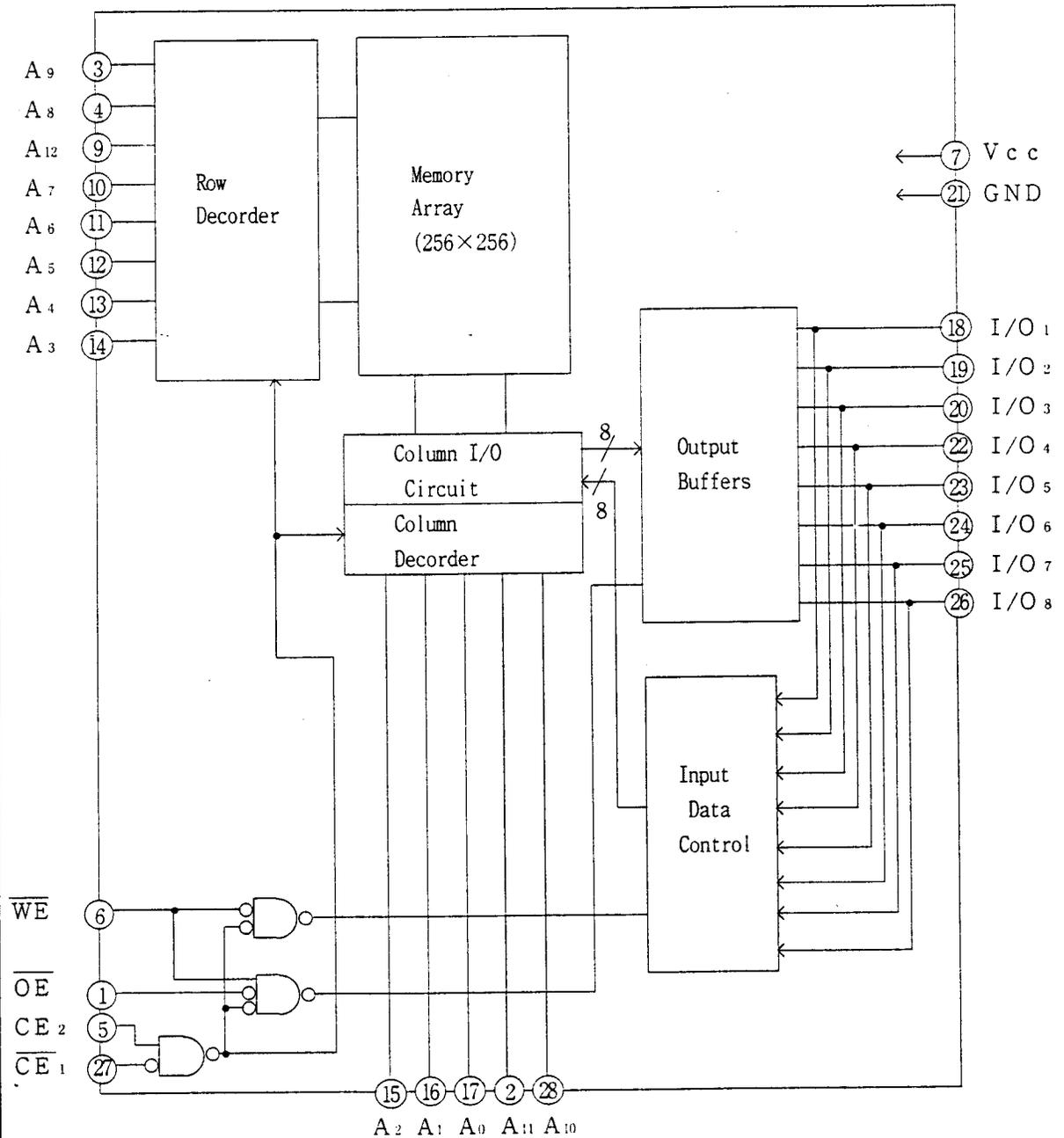
5. Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Supply voltage (*1)	V_{CC}	-0.3 to $+7.0$	V
Input voltage (*1)	V_{IN}	-0.3 (*2) to $V_{CC}+0.3$	V
Operating temperature	T_{opr}	-10 to $+70$	℃
Storage temperature	T_{stg}	-65 to $+150$	℃

Note) *1. The maximum applicable voltage on any pin with respect to GND.
　　　 *2. Undershoot of $-3.0V$ is allowed width of pluse bellow 50ns.

6. Recommended DC Operating Conditions

(Ta= -10℃ to $+70$℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
Input voltage	V_{IH}	2.2		$V_{CC}+0.3$	V
	V_{IL}	-0.3 (*3)		0.8	V

Note) *3. Undershoot of $-3.0V$ is allowed width of pluse below 50ns.

7. DC Electrical Characteristics

(Ta= -10℃ to $+70$℃, Vcc=5 V±10%)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
Input leakage current	I_{LI}	V_{IN}=0V to V_{CC}		-1.0		1.0	μA
Output leakage current	I_{LO}	$\overline{CE_1}$=V_{IH} or CE_2=V_{IL} or $\overline{OE}$=V_{IH} or $\overline{WE}$=V_{IL} $V_{I/o}$=0V to V_{CC}		-1.0		1.0	μA
Operating supply current	I_{CC}	$\overline{CE_1}$=V_{IL}, V_{IN}=V_{IL} or V_{IH} CE_2=V_{IH}, $I_{I/o}$=0mA	t_{CYCLE} = 80ns			55	mA
	I_{CC1}	$\overline{CE_1}$=0.2V, V_{IN}=0.2V or V_{CC}−0.2V CE_2=V_{CC}−0.2V, $I_{I/o}$=0mA	t_{CYCLE} =1.0μs			10	mA
Standby current	I_{SB}	$\overline{CE_1}$, $CE_2 \geq V_{CC}$−0.2V or $CE_2 \leq$0.2V				1.0	μA
	I_{SB1}	$\overline{CE_1}$=V_{IH} or CE_2=V_{IL}				5	mA
Output voltage	V_{OL}	I_{OL}= 2.1mA				0.4	V
	V_{OH}	I_{OH}=-1.0mA		2.4			V

8. AC Electrical Characteristics

AC Test Conditions

Input pulse level	0.6 V to 2.4 V
Input rise and fall time	10 n s
Input and Output timing Ref. level	1.5 V
Output load	1 TTL + C_L (100 p F) (*4)

Note) *4. Including scope and jig capacitance.

Read cycle (Ta = −10℃ to +70 ℃, Vcc = 5 V ± 10%)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Read cycle time	t_{RC}	80			ns
Address access time	t_{AA}			80	ns
$\overline{CE_1}$ access time	t_{ACE1}			80	ns
CE₂ access time	t_{ACE2}			80	ns
Output enable to output valid	t_{OE}			40	ns
Output hold from address change	t_{OH}	10			ns
$\overline{CE_1}$ Low to output active	t_{LZ1}	10			ns
CE₂ High to output active	t_{LZ2}	10			ns
OE Low to output active	t_{OLZ}	5			ns
$\overline{CE_1}$ High to output in High impedance	t_{HZ1}	0		30	ns
CE₂ Low to output in High impedance	t_{HZ2}	0		30	ns
$\overline{OE}$ High to output in High impedance	t_{OHZ}	0		20	ns

Write cycle (Ta = −10℃ to +70 ℃, Vcc = 5 V ± 10%)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Write cycle time	t_{WC}	80			ns
$\overline{CE_1}$ Low to end of write	t_{CW1}	70			ns
CE₂ High to end of write	t_{CW2}	70			ns
Address valid to end of write	t_{AW}	70			ns
Address setup time	t_{AS}	0			ns
Write pluse width	t_{WP}	60			ns
Write recovery time	t_{WR}	0			ns
Input data setup time	t_{DW}	40			ns
Input data hold time	t_{DH}	0			ns
$\overline{WE}$ High to output active	t_{OW}	10			ns
$\overline{WE}$ Low to output in High impedance	t_{WZ}	0		30	ns
$\overline{OE}$ High to output in High impedance	t_{OHZ}	0		20	ns

9. Data Retention Characteristics

$(Ta = -10\,^\circ C\ to +70\,^\circ C)$

Paramenter	Symbol	Conditions		Min.	Typ.	Max.	Unit
Data Retention supply voltage	V_{CCDR}	$CE_2 \leqq 0.2V$ or $\overline{CE}_1 \geqq V_{CCDR} - 0.2V$ (*5)		2.0		5.5	V
Data Retention supply current	I_{CCDR}	$V_{CCDR} = 3V$ $CE_2 \leqq 0.2$ or $\overline{CE}_1 \geqq V_{CCDR} - 0.2V$ (*5)	$Ta = 25\,^\circ C$			0.2	μA
			$Ta = 40\,^\circ C$			0.4	μA
						0.6	μA
Chip enable setup time	t_{CDR}			0			ns
Chip enable hold time	t_R			(*6) t_{RC}			ns

Note) *5. $CE_2 \geqq V_{CCDR} - 0.2V$ or $CE_2 \leqq 0.2V$
*6. Read Cycle

10. Pin Capacitance

$(Ta = 25\,^\circ C,\ f = 1MHz)$

| Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Input capacitance	C_{IN}	$V_{IN} = 0V$			7	pF	*7
I/O capacitance	$C_{I/O}$	$V_{I/O} = 0V$			10	pF	*7

Note) *7. This parameter is sampled and not production tested.

11. Timing Chart

Read cycle timing chart — (*8)
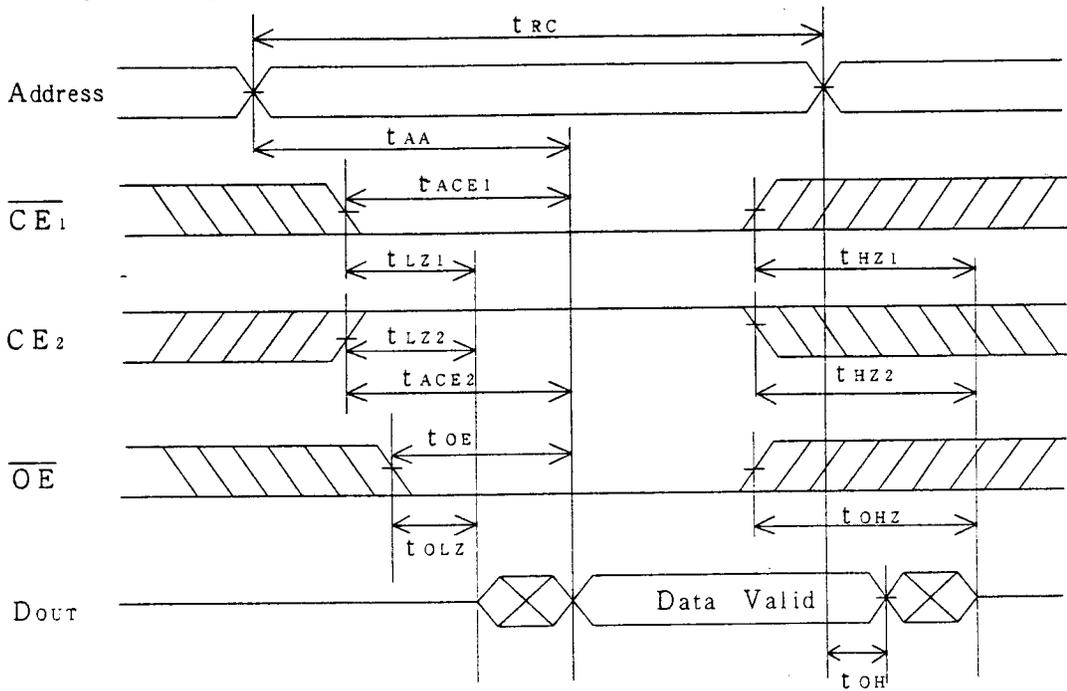
Note) *8. $\overline{WE}$ is high for Read cycle.

Write cycle timing chart — ($\overline{OE}$ Controlled)
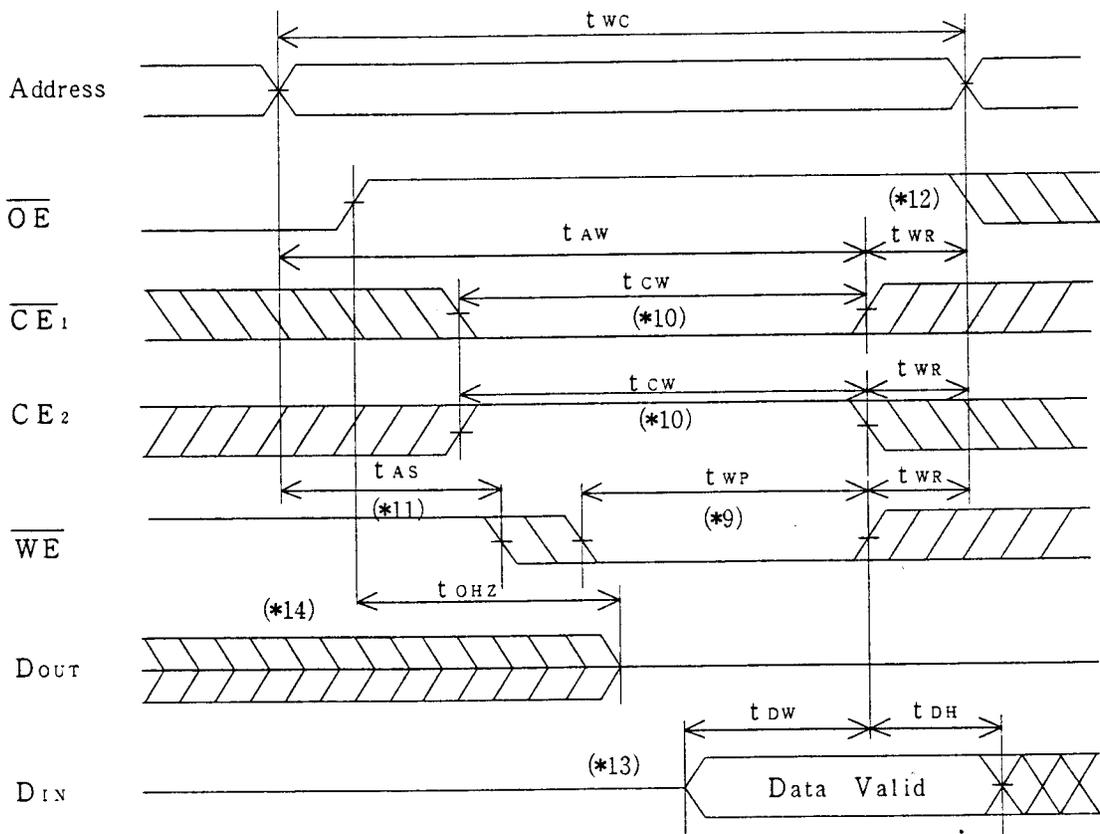
Write cycle timing chart — (OE Low fixed)
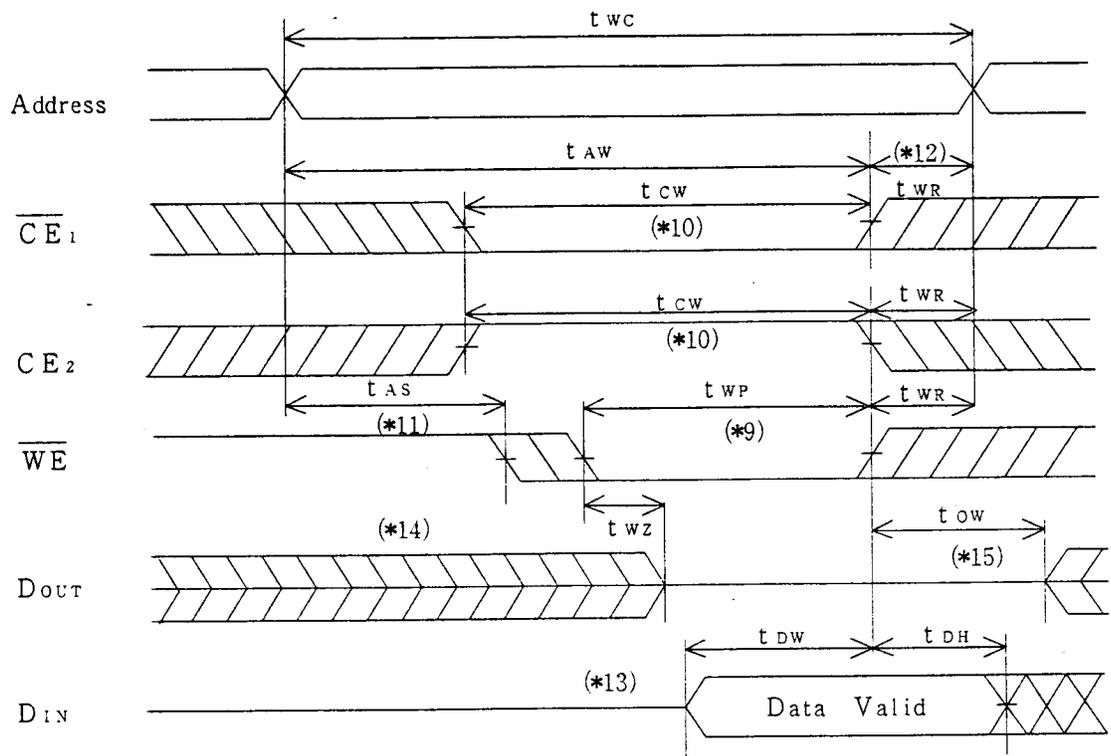
Note) * 9. A write occurs during the overlap of a low CE₁, a high CE₂ and a low WE,

A write begins at the latest transition among CE₁ going low, CE₂ going high

and WE going low.

A write ends at the earliest transition among CE₁ going high, CE₂ going low

and WE going high. t_WP is measured from the beginning of write to the end of write.

* 10. t_CW is measured from the later of CE₁ going low or CE₂ going high

to the end of write.

* 11. t_AS is measured from the address valid to the beginning of write.

* 12. t_WR is measured from the end of write to the address change. t_WR1 applies

in case a write ends at CE₁ or WE going high. t_WR2 applies in case a write ends

at CE₂ going low.

* 13. During this period, I/O pins are in the output state, therefore the input signals

of opposite phase to the outputs must not be applied.

* 14. If CE₁ goes low simultaneously with WE going low or after WE going low,

the outputs remain in high impedance state.

* 15. If CE₁ goes high simultaneously with WE going high or before WE going high,

the outputs remain in high impedance state.

Data Retention timing chart — $\overline{CE_1}$ Controlled)   (*16)

Data Retention mode

V_{CC}

4.5 V

t_{CDR} t_R

2.2 V

V_{CCDR}

$\overline{CE_1} \geqq V_{CCDR} - 0.2V$

$\overline{CE_1}$

0 V
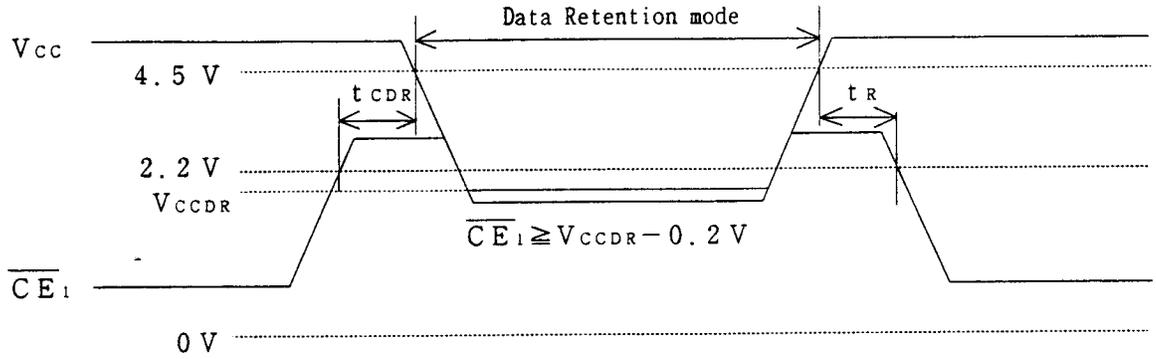
Data Retention timing chart — (CE₂ Controlled)

Data Retention mode

V_{CC}

4.5 V

CE_2

t_{CDR} t_R

V_{CCDR}

0.8 V

$CE_2 \leqq 0.2V$

0 V
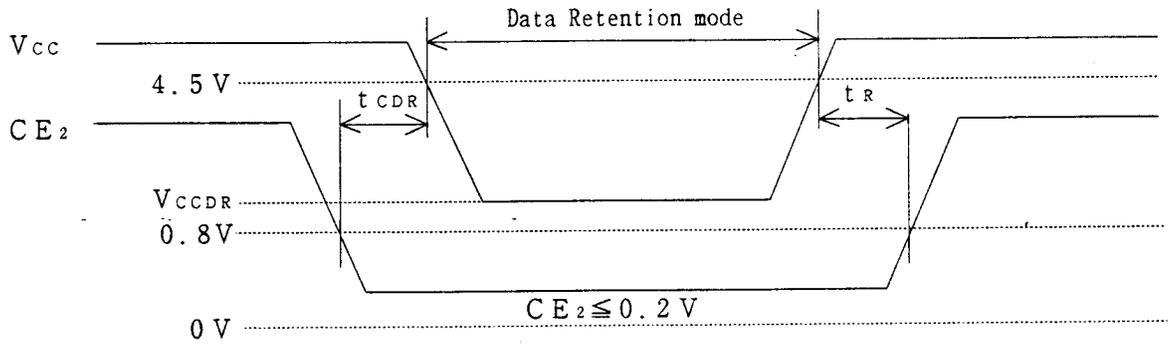
Note) *16. To control the data retention mode at $\overline{CE_1}$, fix the input level of CE₂ between V_{CCDR} and $V_{CCDR} - 0.2V$ or 0V and 0.2V during the data retention mode.

STATIC SRAM RAM Random Access Memory TSOP LH5164AT-80L CMOS 64K (8K x 8)